Medium power transistor (30V, 2A) 2SC5916

● Features

- 1) High speed switching. (Tf: Typ.: 20ns at Ic = 2A)
- 2) Low saturation voltage, typically

(Typ.: 200mV at Ic = 1.0A, IB = 0.1A)

- 3) Strong discharge power for inductive load and capacitance load.
- 4) Complements the 2SA2113

Applications

Low frequency amplifier High speed switching

●Structure

NPN Silicon epitaxial planar transistor

Packaging specifications

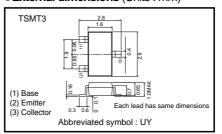
Туре	Package	Taping
	Code	TL
	Basic ordering unit (pieces)	3000
2SC5916		0

●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	Vсво	30	V
Collector-emitter voltage	Vceo	30	V
Emitter-base voltage	VEBO	6	V
Collector current	Ic	2	А
Collector current	Іср	4	A *1
Power dissipation	Pc	500	mW *2
Junction temperature	Tj	150	°C
Range of storage temperature	Tstg	−55~+150	°C

^{*1} Pw=10ms

●External dimensions (Units: mm)



^{*2} Each terminal mounted on a recommended land.

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-base breakdown voltage	BVceo	30	-	-	V	Ic=100μA
Collector-emitter breakdown voltage	ВУсво	30	-	_	V	Ic=1mA
Emitter-base breakdown voltage	ВУево	6	_	_	V	IE=100μA
Collector cut-off current	Ісво	_	_	1.0	μΑ	Vcb=20V
Emitter cut-off current	ІЕВО	=	-	1.0	μΑ	V _{EB} =4V
Collector-emitter staturation voltage	VCE(sat)	-	200	400	mV	Ic=1.0A, I _B =0.1A
DC current gain	hfe	120	_	390	_	VcD=2V, Ic=100mA
Transition frequency	fT	_	250	_	MHz	Vce=10V, Ie=-100mA, f=10MHz
Collector output capacitance	Cob	_	15	_	pF	Vcb=10V, IE=0, f=1MHz
Turn-on time	Ton	_	25	_	ns	Ic=2A
Storage time	Tstg	_	100	_	ns	IB1=200mA
Fall time	Tf	_	20	_	ns	Vcc≒-25V

●hFE RANK

Q	R
120-270	180-390

Electrical characteristic curves

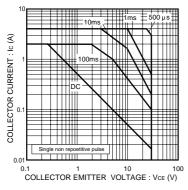


Fig.1 Safe operating area

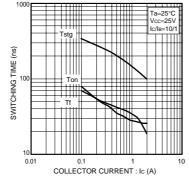


Fig.2 Switching Time

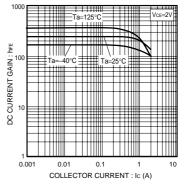


Fig.3 DC current gain vs. collector

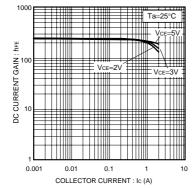
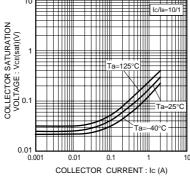


Fig.4 DC current gain vs. collector current



vs. collector current

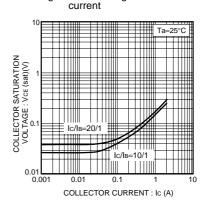
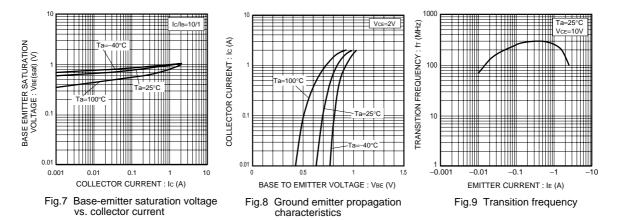


Fig.5 Collector-emitter saturation voltage Fig.6 Collector-emitter saturation voltage vs. collector current



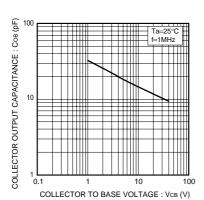
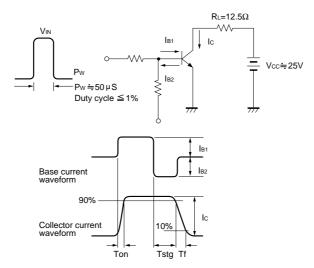


Fig.10 Collector output capacitance

•Switching characteristics measurement circuits



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